8-Bit Serial-Input/Serial or Parallel-Output Shift Register with Latched 3-State Outputs

High-Performance Silicon-Gate CMOS

MC74HC595A

The MC74HC595A consists of an 8-bit shift register and an 8-bit D-type latch with three-state parallel outputs. The shift register accepts serial data and provides a serial output. The shift register also provides parallel data to the 8-bit latch. The shift register and latch have independent clock inputs. This device also has an asynchronous reset for the shift register.

The HC595A directly interfaces with the SPI serial data port on CMOS MPUs and MCUs.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 328 FETs or 82 Equivalent Gates
- Improvements over HC595
 - Improved Propagation Delays
 - ◆ 50% Lower Quiescent Power
 - Improved Input Noise and Latchup Immunity
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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SOIC-16 D SUFFIX CASE 751B

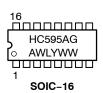


TSSOP-16 DT SUFFIX CASE 948F



QFN16 MN SUFFIX CASE 485AW

MARKING DIAGRAMS





TSSOP-16

595A ALYW■ ○ ■

QFN16*

*V595A marking used for NLV74HC595AMN1TWG

A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G, • = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 11 of this data sheet.

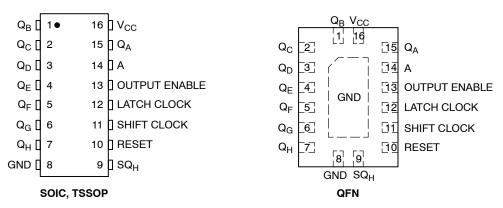
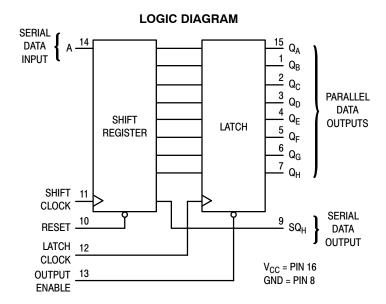


Figure 1. Pin Assignments



MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V _{CC} +0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} +0.5	V
I _{in}	DC Input Current, per Pin	±20	mA
I _{out}	DC Output Current, per Pin	±35	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±75	mA
P _D	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	> 3000 > 400 N/A	V

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: -7 mW/°C from 65° to 125°C

TSSOP Package: -6.1 mW/°C from 65° to 125°C

- 1. Tested to EIA/JESD22-A114-A.
- 2. Tested to EIA/JESD22-A115-A.
- 3. Tested to JESD22-C101-A.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V	
T _A	Operating Temperature, All Package Types		– 55	+125	°C
t _r , t _f	(Figure 1)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				V _{CC}	Guar			
Symbol	Parameter	Test Cond	itions	v	–55 to 25°C	≤ 85 ° C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	V_{out} = 0.1 V or V_{CC} $ I_{out} \le 20 \mu A$	– 0.1 V	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low-Level Input Voltage	V_{out} = 0.1 V or V_{CC} $ I_{out} \le 20 \mu A$	V_{out} = 0.1 V or V_{CC} – 0.1 V $ I_{out} \le 20 \mu A$		0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V _{OH}	Minimum High-Level Output Voltage, Q _A – Q _H	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$		2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{in} = V_{IH}$ or V_{IL}	$\begin{aligned} & I_{out} \leq 2.4 \text{ mA} \\ & I_{out} \leq 6.0 \text{ mA} \\ & I_{out} \leq 7.8 \text{ mA} \end{aligned}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	
V _{OL}	Maximum Low-Level Output Voltage, Q _A – Q _H	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$		2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{in} = V_{IH}$ or V_{IL}	$\begin{aligned} & \left I_{out}\right \leq 2.4 \text{ mA} \\ & \left I_{out}\right \leq 6.0 \text{ mA} \\ & \left I_{out}\right \leq 7.8 \text{ mA} \end{aligned}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	
V _{OH}	Minimum High-Level Output Voltage, SQ _H	$V_{in} = V_{IH} \text{ or } V_{IL}$ $II_{out}I \le 20 \mu A$		2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{in} = V_{IH}$ or V_{IL}	$\begin{aligned} & I_{out} \leq 2.4 \text{ mA} \\ & II_{out}I \leq 4.0 \text{ mA} \\ & Ii_{out}I \leq 5.2 \text{ mA} \end{aligned}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	
V _{OL}	Maximum Low-Level Output Voltage, SQ _H	$V_{in} = V_{IH} \text{ or } V_{IL}$ $II_{out}I \le 20 \mu A$		2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{in} = V_{IH}$ or V_{IL}	$\begin{aligned} & \left I_{out}\right \leq 2.4 \text{ mA} \\ & II_{out}I \leq 4.0 \text{ mA} \\ & Ii_{out}I \leq 5.2 \text{ mA} \end{aligned}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND		6.0	±0.1	±1.0	±1.0	μΑ
I _{OZ}	Maximum Three-State Leakage Current, Q _A – Q _H	Output in High-Imp $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	edance State	6.0	±0.5	±5.0	±10	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$		6.0	4.0	40	160	μΑ

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6.0 ns)

		V _{CC}	Guar	İ		
Symbol	Parameter	v	–55 to 25°C	≤ 85 °C	≤ 125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 7)	2.0 3.0 4.5 6.0	6.0 15 30 35	4.8 10 24 28	4.0 8.0 20 24	MHz
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Shift Clock to SQ _H (Figures 1 and 7)	2.0 3.0 4.5 6.0	140 100 28 24	175 125 35 30	210 150 42 36	ns
t _{PHL}	Maximum Propagation Delay, Reset to SQ _H (Figures 2 and 7)	2.0 3.0 4.5 6.0	145 100 29 25	180 125 36 31	220 150 44 38	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Latch Clock to Q _A – Q _H (Figures 3 and 7)	2.0 3.0 4.5 6.0	140 100 28 24	175 125 35 30	210 150 42 36	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Q _A – Q _H (Figures 4 and 8)	2.0 3.0 4.5 6.0	150 100 30 26	190 125 38 33	225 150 45 38	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Q _A – Q _H (Figures 4 and 8)	2.0 3.0 4.5 6.0	135 90 27 23	170 110 34 29	205 130 41 35	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Q _A – Q _H (Figures 3 and 7)	2.0 3.0 4.5 6.0	60 23 12 10	75 27 15 13	90 31 18 15	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, SQ _H (Figures 1 and 7)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C _{in}	Maximum Input Capacitance	-	10	10	10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State), Q _A - Q _H	-	15	15	15	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Package)*	300	pF

TIMING REQUIREMENTS (Input $t_r = t_f = 6.0 \text{ ns}$)

		v _{cc}	Guaranteed Limit				
Symbol	Parameter	V	25°C to -55°C	≤ 85 °C	≤ 125°C	Unit	
t _{su}	Minimum Setup Time, Serial Data Input A to Shift Clock	2.0	50	65	75	ns	
	(Figure 5)	3.0	40	50	60		
		4.5	10	13	15		
		6.0	9.0	11	13		
t _{su}	Minimum Setup Time, Shift Clock to Latch Clock	2.0	75	95	110	ns	
	(Figure 6)	3.0	60	70	80		
		4.5	15	19	22		
		6.0	13	16	19		
t _h	Minimum Hold Time, Shift Clock to Serial Data Input A	2.0	5.0	5.0	5.0	ns	
	(Figure 5)	3.0	5.0	5.0	5.0		
		4.5	5.0	5.0	5.0		
		6.0	5.0	5.0	5.0		
t _{rec}	Minimum Recovery Time, Reset Inactive to Shift Clock	2.0	50	65	75	ns	
	(Figure 2)	3.0	40	50	60		
		4.5	10	13	15		
		6.0	9.0	11	13		
t _w	Minimum Pulse Width, Reset	2.0	60	75	90	ns	
	(Figure 2)	3.0	45	60	70		
		4.5	12	15	18		
		6.0	10	13	15		
t_w	Minimum Pulse Width, Shift Clock	2.0	50	65	75	ns	
	(Figure 1)	3.0	40	50	60		
		4.5	10	13	15		
		6.0	9.0	11	13		
t _w	Minimum Pulse Width, Latch Clock	2.0	50	65	75	ns	
	(Figure 6)	3.0	40	50	60		
		4.5	10	13	15		
		6.0	9.0	11	13		
t_r,t_f	Maximum Input Rise and Fall Times	2.0	1000	1000	1000	ns	
	(Figure 1)	3.0	800	800	800		
		4.5	500	500	500		
		6.0	400	400	400		

FUNCTION TABLE

	Inputs						Resulting Function				
Operation	Reset	Serial Input A	Shift Clock	Latch Clock	Output Enable	Shift Register Contents	Latch Register Contents	Serial Output SQ _H	Parallel Outputs Q _A – Q _H		
Reset shift register	L	Х	Х	L, H, ↓	L	L	U	L	U		
Shift data into shift register	Н	D	1	L, H, ↓	L	$\begin{array}{c} \text{D} \rightarrow \text{SR}_{A};\\ \text{SR}_{N} \rightarrow \text{SR}_{N+1} \end{array}$	U	$SR_G \rightarrow SR_H$	U		
Shift register remains unchanged	Н	Х	L, H, ↓	L, H, ↓	L	U	U	U	U		
Transfer shift register contents to latch register	Н	Х	L, H, ↓	1	L	U	$SR_N \rightarrow LR_N$	U	SR _N		
Latch register remains unchanged	Х	Х	Х	L, H, ↓	L	*	U	*	U		
Enable parallel outputs	Х	Х	Х	Х	L	*	**	*	Enabled		
Force outputs into high impedance state	Х	Х	Х	Х	Н	*	**	*	Z		

SR = shift register contents

D = data (L, H) logic level

↑ = Low-to-High

* = depends on Reset and Shift Clock inputs

U = remains unchanged

 \downarrow = High-to-Low

** = depends on Latch Clock input

PIN DESCRIPTIONS

INPUTS A (Pin 14)

Serial Data Input. The data on this pin is shifted into the 8-bit serial shift register.

CONTROL INPUTS Shift Clock (Pin 11)

Shift Register Clock Input. A low-to-high transition on this input causes the data at the Serial Input pin to be shifted into the 8-bit shift register.

Reset (Pin 10)

Active-low, Asynchronous, Shift Register Reset Input. A low on this pin resets the shift register portion of this device only. The 8-bit latch is not affected.

Latch Clock (Pin 12)

Storage Latch Clock Input. A low-to-high transition on this input latches the shift register data.

Output Enable (Pin 13)

Active-low Output Enable. A low on this input allows the data from the latches to be presented at the outputs. A high on this input forces the outputs (QA-QH) into the high-impedance state. The serial output is not affected by this control unit.

OUTPUTS

Q_A - Q_H (Pins 15, 1, 2, 3, 4, 5, 6, 7)

Noninverted, 3-state, latch outputs.

SQ_H (Pin 9)

Noninverted, Serial Data Output. This is the output of the eighth stage of the 8-bit shift register. This output does not have three-state capability.

LR = latch register contents

SWITCHING WAVEFORMS

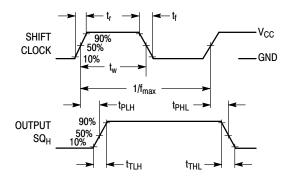


Figure 1.

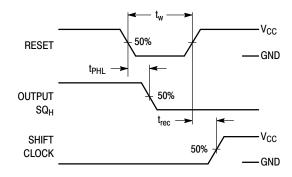


Figure 2.

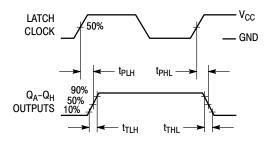


Figure 3.

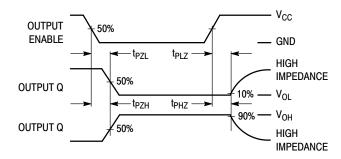


Figure 4.

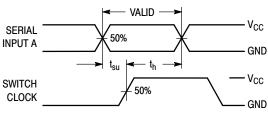


Figure 5.

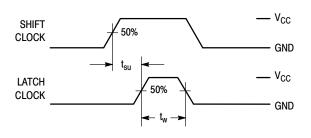
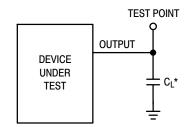


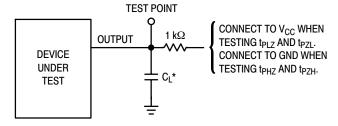
Figure 6.

TEST CIRCUITS



*Includes all probe and jig capacitance

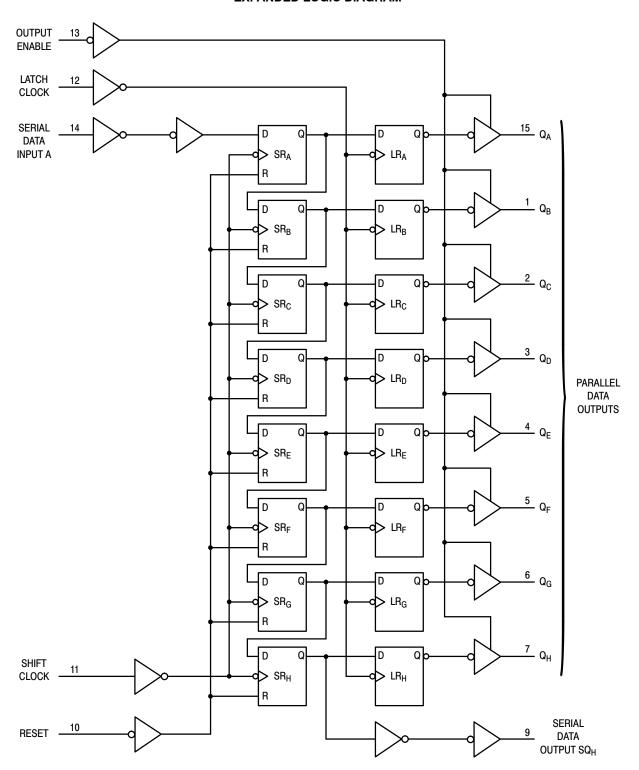
Figure 7.



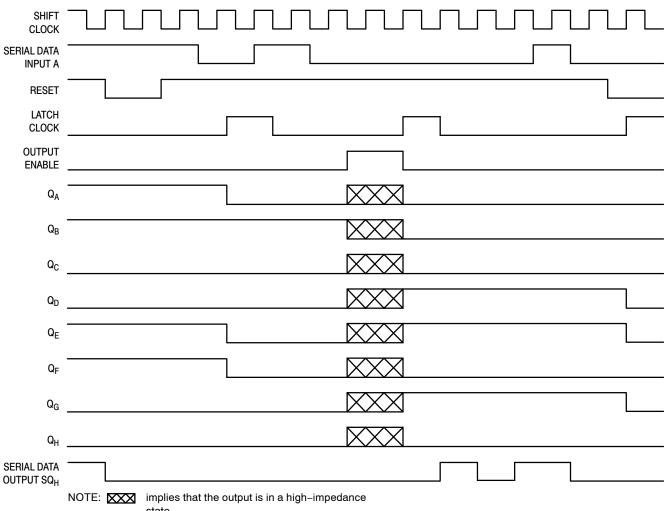
*Includes all probe and jig capacitance

Figure 8.

EXPANDED LOGIC DIAGRAM



TIMING DIAGRAM



state.

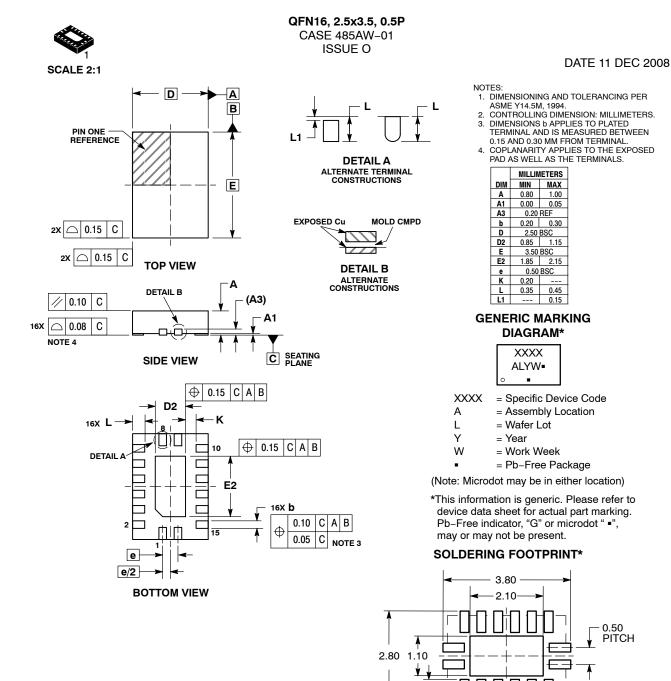
ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC595ADG		48 Units / Rail
NLV74HC595ADG*	7	48 Units / Rail
MC74HC595ADR2G	2010 10	2500 / Tape & Reel
NLV74HC595ADR2G*	SOIC-16 (Pb-Free)	2500 / Tape & Reel
MC74HC595AADR2G	7	2500 / Tape & Reel
NLV74HC595AADR2G* (Contact ON Semiconductor)		2500 / Tape & Reel
MC74HC595ADTG		96 Units / Tube
NLV74HC595ADTG*		96 Units / Tube
MC74HC595ADTR2G	TSSOP-16 (Pb-Free)	2500 / Tape & Reel
NLV74HC595ADTR2G*	(= 1123)	2500 / Tape & Reel
NLV74HC595AADTR2G*		2500 / Tape & Reel
MC74HC595AMNTWG#		3000 / Tape & Reel
NLV74HC595AMNTWG*#	QFN16 (Pb-Free)	3000 / Tape & Reel
NLV74HC595AMN1TWG*#		3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#MN suffix is with pull-back lead, MN1 is without pull-back lead. Refer to 'Detail A' of case outline on page 13.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

16X

0.30

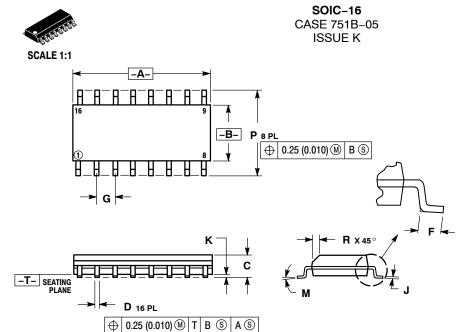
DIMENSIONS: MILLIMETERS

DOCUMENT NUMBER:	98AON36347E	Printed versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED (
DESCRIPTION:	QFN16, 2.5X3.5, 0.5P		PAGE 1 OF 1

16X 0.60

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PACKAGE



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35 0.49		0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050) BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80 6.20		0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.	COLLECTOR	PIN 1.	CATHODE		COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE	E #1	
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE	13.	CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	COL DEDING	FOOTPRINT
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDERING	FOOTPRINT
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1		8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1		5.40 >
									.40
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12 -
PIN 1.	DRAIN, DYE #1		CATHODE		SOURCE N-CH				, ''
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPUT	Γ\		. 🔲 1	16
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPUT			, .	" 🗀
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	٠,		- —	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT	Γ\	4.	₆	
6.	DRAIN. #3	6.	CATHODE	6.	COMMON DRAIN (OUTPUT			^{6X}	<u> </u>
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPUT		0.	56	
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	.,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT	Γ)			
11.	,	11.	ANODE	11.	COMMON DRAIN (OUTPUT				
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPUT				
13.	GATE, #2	13.		13.	GATE N-CH	,			
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPUT	Γ)			— PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT				<u>+-+</u> -
16.	SOURCE, #1	16.	ANODE	16.					
								Пв	9 + - + -
									_
									DIMENSIONS, MILLIMETERS
									DIMENSIONS: MILLIMETERS

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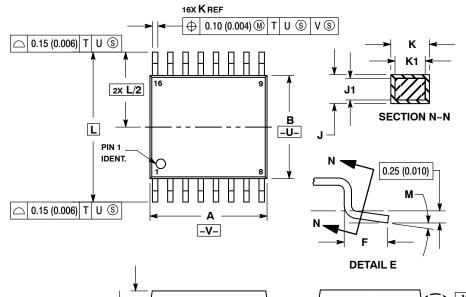
D.

-T- SEATING PLANE



TSSOP-16 CASE 948F-01 ISSUE B

DATE 19 OCT 2006



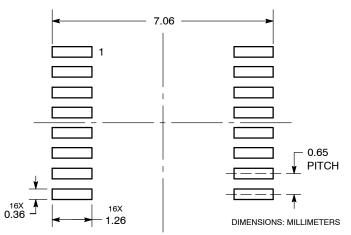
NOTES

- JIES:
 DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD
 FLASH. PROTRUSIONS OR GATE BURRS.
 MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	٥°	8 °	٥°	8 °



G



GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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